

Silicon NPN Power Transistors

2SC1450

DESCRIPTION

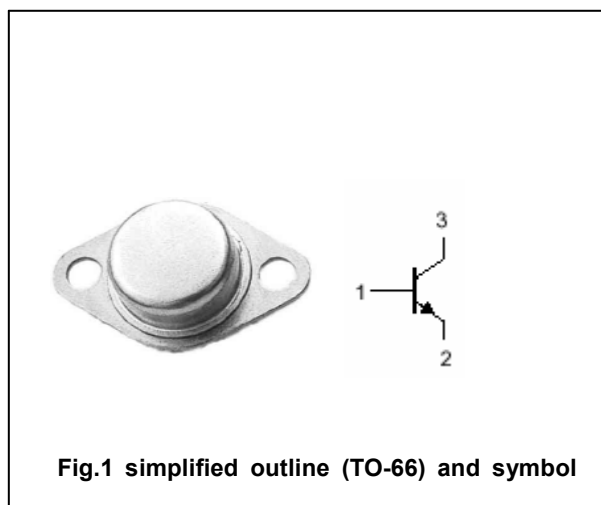
- With TO-66 package
- Wide area of safe operation
- High collector-emitter breakdown voltage
: $V_{CEO}=150V(\text{min})$
- Complement to type 2SA766

APPLICATIONS

- For power amplifier and vertical output applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=\square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		0.4	A
P_D	Total power dissipation	$T_C=80\square$	20	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-65~200	\square

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =30mA; I _B =0	150			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA; I _E =0	150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =0.5A; I _B =50m A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =150V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE}	DC current gain	I _C =0.1A ; V _{CE} =5V	30		150	

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PACKAGE OUTLINE



Fig.2 outline dimensions